



# ACE16015B

## N-Channel Enhancement Mode Power MOSFET

### General Description

- DC Motor Driver
- Synchronous Rectification in DC/DC
- AC/DC Converters

### Features

- $V_{DS}=60V$
- $I_D=153A$
- $R_{DS(ON)}@V_{GS}=10V$ , TYP 2.5m $\Omega$  (TO-220)
- $R_{DS(ON)}@V_{GS}=4.5V$ , TYP 3.5m $\Omega$  (TO-220)
- $R_{DS(ON)}@V_{GS}=10V$ , TYP 2.4m $\Omega$  (TO-263-3)
- $R_{DS(ON)}@V_{GS}=4.5V$ , TYP 3.5m $\Omega$  (TO-263-3)

### Absolute Maximum Ratings

Parameter	Symbol	Ratings	Units	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V	
Drain Current (Continuous) *AC	$I_D$	$T_C=25^\circ C$	153	A
		$T_C=100^\circ C$	96.7	
Drain Current (Pulsed) *B	$I_{DM}$	540	A	
Power Dissipation	$P_D$	$T_C=25^\circ C$	139	W
Operating temperature / storage temperature	$T_J/T_{STG}$	-55~150	$^\circ C$	

Note:

A. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ . The value in any given application depends on the user's specific board design.

B. Repetitive rating, pulse width limited by junction temperature.

C. The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating

### Thermal Resistance Ratings

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case (Drain)      Steady State	$R_{thJC}$	0.9	$^\circ C/W$

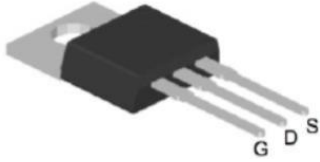


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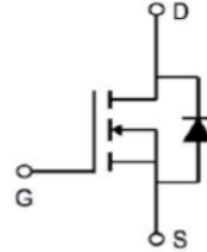
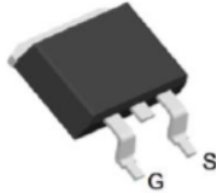
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## Packaging Type

TO-220

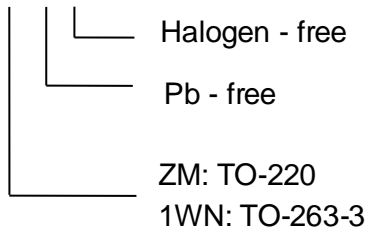


TO-263-3



## Ordering information

ACE16015B XX + H





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## N-Channel Enhancement Mode Power MOSFET

**Electrical Characteristics**  $T_A=25^{\circ}\text{C}$ , unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu A$
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_{DS} = 250\mu A$	1	2	3	V
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Drain-Source On-state Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 30A$ (TO-220)		2.5	3.3	m $\Omega$
		$V_{GS} = 4.5V, I_D = 20A$ (TO-220)		3.5	4.6	
		$V_{GS} = 10V, I_D = 30A$ (TO-263-3)		2.4	3.1	
		$V_{GS} = 4.5V, I_D = 20A$ (TO-263-3)		3.5	4.6	
Diode Forward Voltage	$V_{SD}$	$I_{SD} = 1A, V_{GS} = 0V$		0.68	1.2	V
Diode Forward Current	$I_S$	$T_C = 25^{\circ}\text{C}$			153	A
Switching						
Total Gate Charge	$Q_g$	$V_{GS} = 10V, V_{DS} = 48V,$ $I_D = 30A$		138		nC
Gate-Source Charge	$Q_{gs}$			34		
Gate-Drain Charge	$Q_{gd}$			46		
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 30V,$ $R_{GEN} = 3.6\Omega, I_D = 30A$		34		ns
Turn-on Rise Time	$t_r$			23		
Turn-off Delay Time	$t_{d(off)}$			82		
Turn-Off Fall Time	$t_f$			25		
Dynamic						
Input Capacitance	$C_{iss}$	$V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$		6010		pF
Output Capacitance	$C_{oss}$			1150		
Reverse Transfer Capacitance	$C_{rss}$			60		



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Typical Performance Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

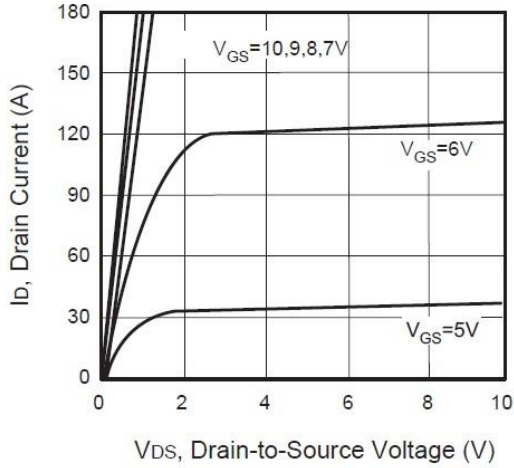


Figure 1. Output Characteristics

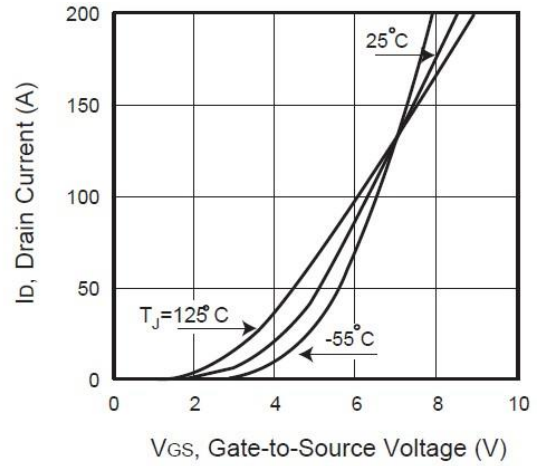


Figure 2. Transfer Characteristics

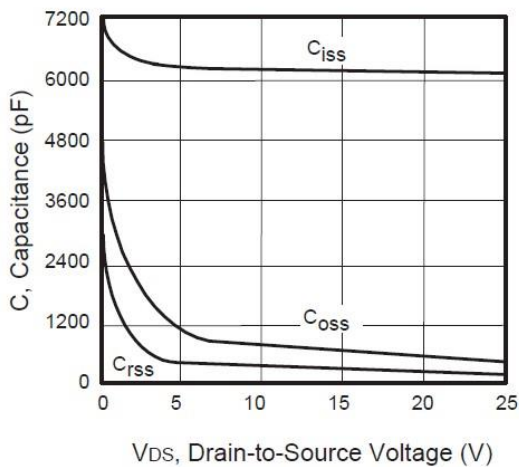


Figure 3. Capacitance

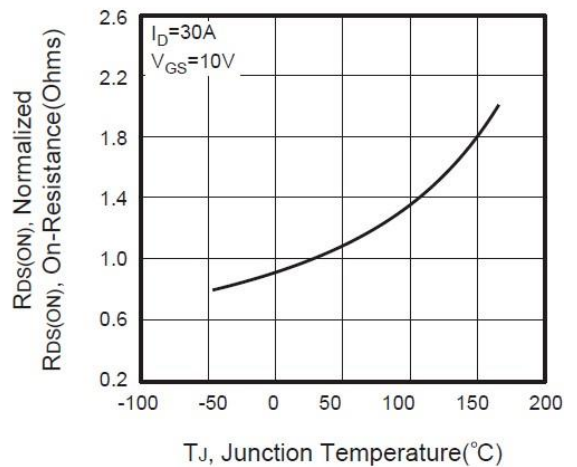


Figure 4. On-Resistance Variation with Temperature

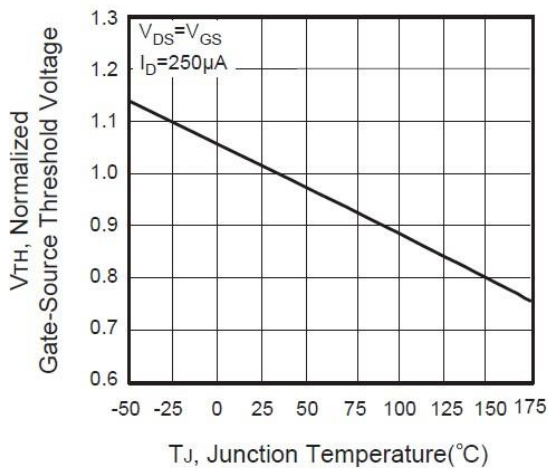


Figure 5. Gate Threshold Variation with Temperature

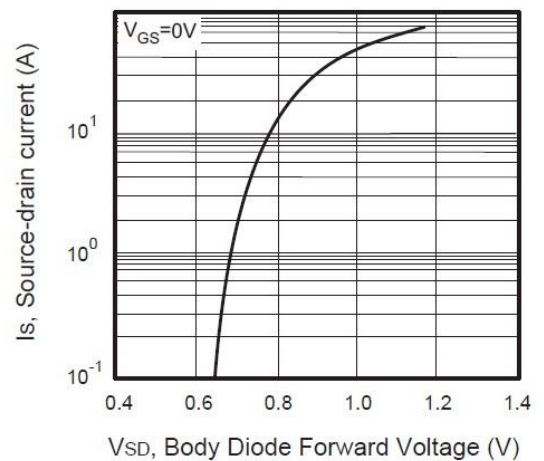


Figure 6. Body Diode Forward Voltage Variation with Source Current



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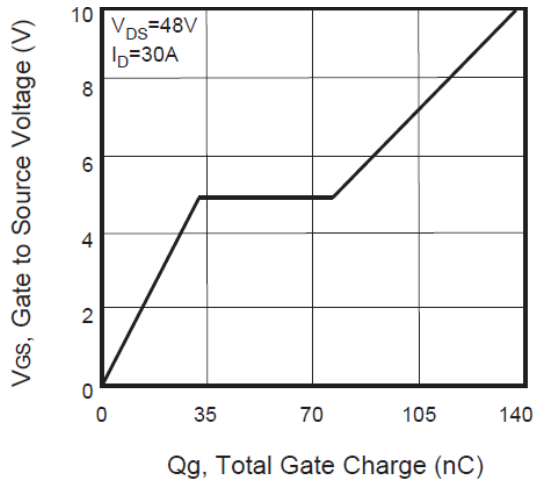


Figure 7. Gate Charge

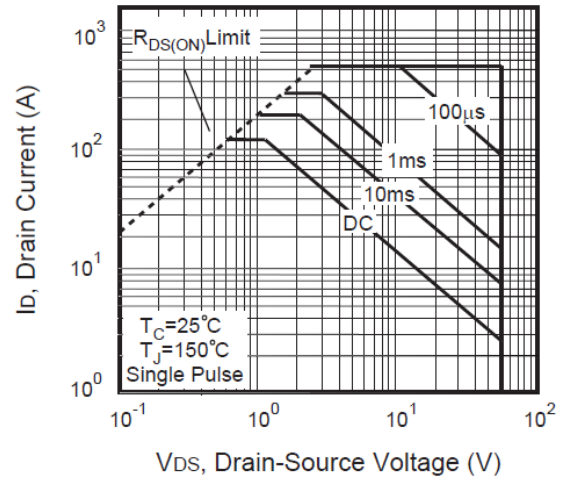


Figure 8. Maximum Safe Operating Area

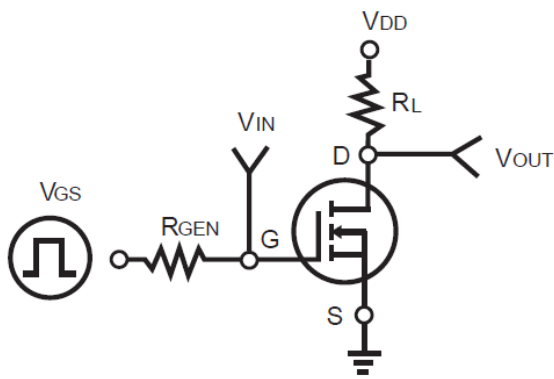


Figure 9. Switching Test Circuit

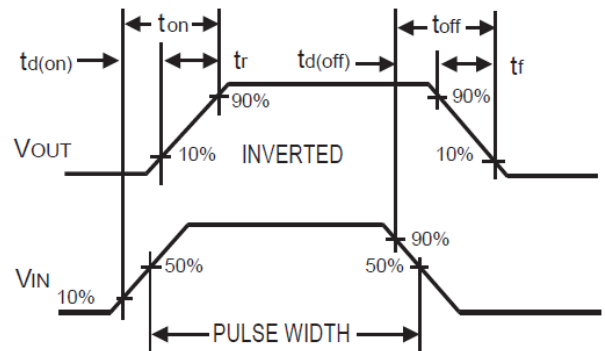


Figure 10. Switching Waveforms

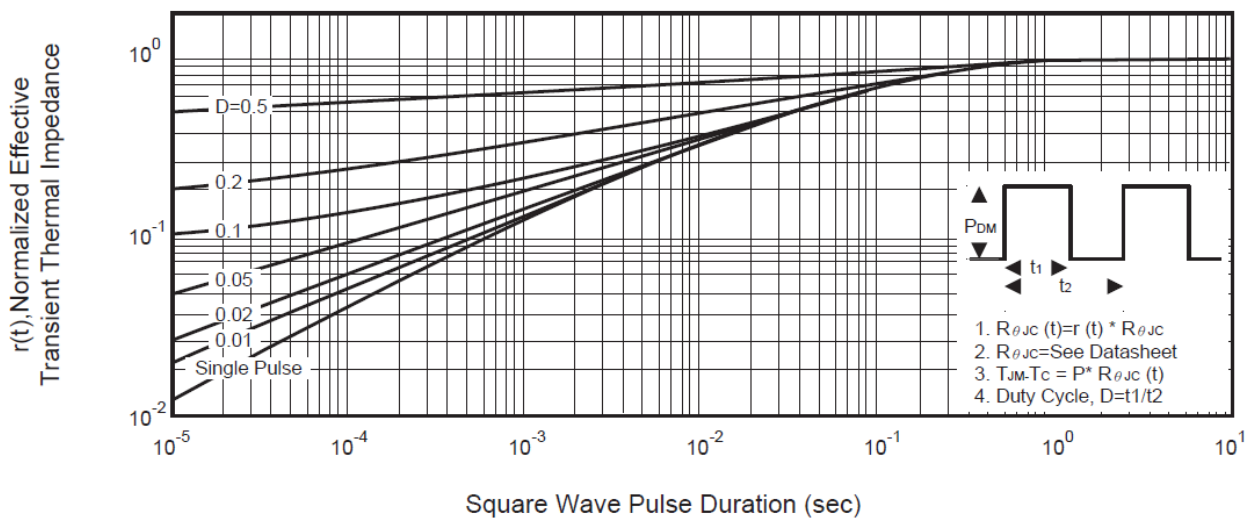


Figure 11. Normalized Thermal Transient Impedance Curve

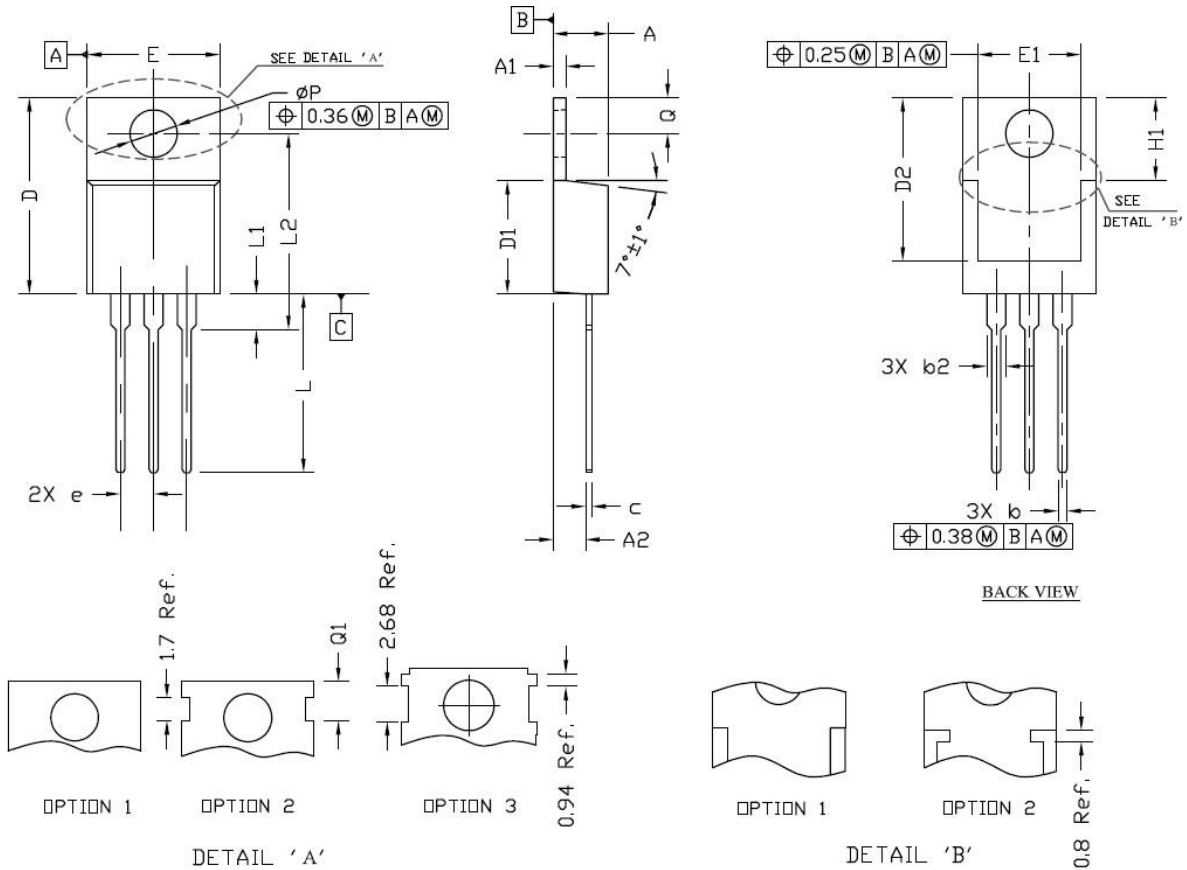


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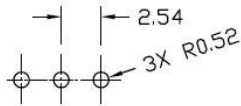
## N-Channel Enhancement Mode Power MOSFET

### Packing Information

TO-220



#### RECOMMENDATION OF HOLE PATTERN



UNIT: mm

#### NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MIL.
2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
3. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.45	4.72	0.169	0.175	0.186
A1	1.15	1.27	1.40	0.045	0.050	0.055
A2	2.20	2.67	2.90	0.087	0.105	0.114
b	0.69	0.81	0.95	0.027	0.032	0.037
b2	1.17	1.37	1.45	0.046	0.050	0.068
c	0.36	0.38	0.60	0.014	0.015	0.024
D	14.50	15.44	15.80	0.571	0.608	0.622
D1	8.59	9.14	9.65	0.338	0.360	0.380
D2	11.43	11.73	12.48	0.450	0.462	0.491
e	2.54 BSC.			0.100 BSC.		
E	9.66	10.03	10.54	0.380	0.395	0.415
E1	6.22	---	---	0.245	---	---
H1	6.10	6.30	6.50	0.240	0.248	0.256
L	12.27	12.82	14.27	0.483	0.505	0.562
L1	2.47	---	3.90	0.097	---	0.154
L2	---	---	16.70	---	---	0.657
Q	2.59	2.74	2.89	0.102	0.108	0.114
ØP	3.50	3.84	3.89	0.138	0.151	0.153
Q1	2.70	---	2.90	0.106	---	0.114

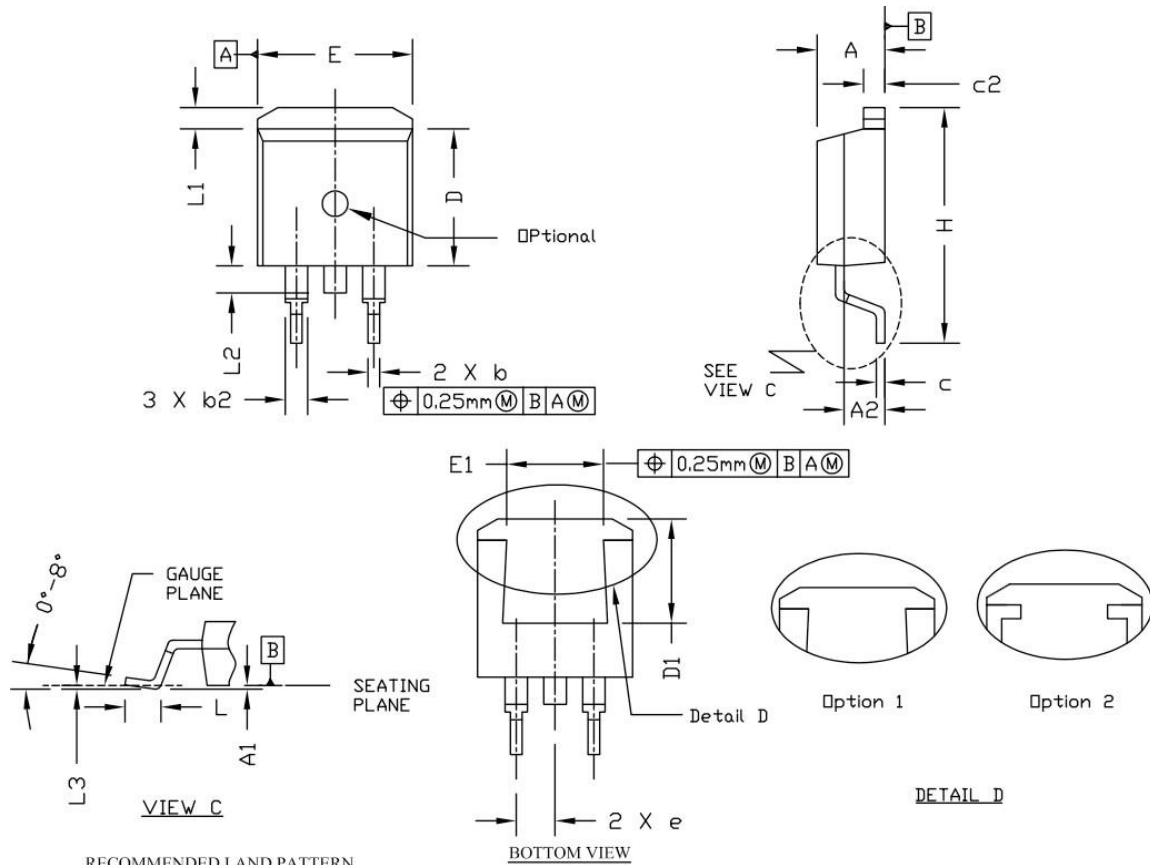


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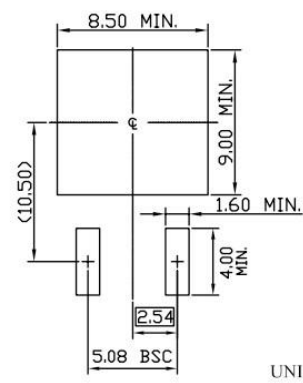
## N-Channel Enhancement Mode Power MOSFET

### Packing Information

TO-263-3



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.064	4.45	4.826	0.160	0.175	0.190
A1	0.00	---	0.254	0.000	---	0.010
A2	2.20	2.67	2.90	0.087	0.105	0.114
b	0.508	0.81	0.991	0.020	0.032	0.039
b2	1.143	1.27	1.778	0.045	0.050	0.070
c	0.381	0.50	0.737	0.015	0.020	0.029
c2	1.143	1.27	1.651	0.045	0.050	0.065
D	8.382	9.14	9.652	0.330	0.360	0.380
D1	6.858	8.00	8.37	0.270	0.315	0.330
e	2.54 BSC			0.100 BSC.		
E	9.652	10.03	10.668	0.380	0.395	0.420
E1	6.223	8.00	8.37	0.245	0.315	0.330
H	14.605	15.24	15.875	0.575	0.600	0.625
L	1.778	2.54	2.794	0.070	0.100	0.110
L1	1.02	1.27	1.676	0.040	0.050	0.066
L2	1.27	1.52	1.778	0.50	0.60	0.070
L3	0.25 BSC			0.010 BSC.		

- NOTE:
1. PACKAGE BODY SIDES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MILS.
  2. TOLERANCE 0.10 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
  3. DIMENSION L IS MEASURED IN GAUGE LINE.
  4. CONTROLLING DIMENSION IS MILLIMETER.
  5. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT. REFER TO JEDEC TO-263 AB.



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### Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Technology Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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